



BOX AFTER FINAL  
EXPEDITED PROCEDURE  
740756-1996

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of:

Shunpei YAMAZAKI et al.

Application No.: 09/352,362

Filed: July 13, 1999

For: CRYSTALLINE SEMICONDUCTOR THIN FILM)  
METHOD OF FABRICATING THE SAME,  
SEMICONDUCTOR DEVICE, AND METHOD  
OF FABRICATING THE SAME

)  
)  
) Art Unit: 2815  
)  
) Examiner: Jose R. Diaz

) CERTIFICATE OF MAILING

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AMENDMENT UNDER 37 C.F.R. 1.116

Commissioner of Patents  
Washington, D.C. 20231

December 12, 2001

Dear Sir:

In response to the Examiner's Final Office Action mailed July 18, 2001, please consider the following amendments and remarks in connection with the above-identified application.

IN THE CLAIMS:

Please amend claims 15, 17, 20, 22, 25, 28, 30, 31, 34, and 35 to read as follows:

Sub  
DIE 17  
15. (Amended) A method of fabricating a semiconductor device comprising:  
adding an element for facilitating crystallization of an amorphous semiconductor thin film to at least a portion of the amorphous semiconductor thin film;  
carrying out a first heat treatment to transform the at least a portion of the amorphous semiconductor thin film into a crystalline semiconductor thin film;  
carrying out a second heat treatment for the crystalline semiconductor thin film at 900 to 1200°C in a reducing atmosphere to flatten a surface of the crystalline semiconductor thin film.

Sub  
DIE 27  
17. (Amended) A method of fabricating a semiconductor device comprising:  
adding an element for facilitating crystallization of an amorphous semiconductor thin film to at least a portion of the amorphous semiconductor thin film;